

Wavelength	Type	Technology	Case
Infrared	SMD	AlGaAs/AlGaAs	TOPLED

	<p>Description</p> <p>Selective photodiode mounted in TOPLED® PLCC-2 package, for easy circuit board mounting and assembling of arrays. Narrow response range (740 nm peak) by means of integrated filter</p>
	<p>Applications</p> <p>Optical communications, safety equipment, light barriers</p>

Miscellaneous Parameters

T_{amb} = 25°C, unless otherwise specified

Parameter	Test conditions	Symbol	Value	Unit
Active area		A	0.09	mm ²
Temperature coefficient of I _D		T _C (I _D)	5	%/K
Operating temperature range		T _{amb}	-20 to +85	°C
Storage temperature range		T _{stg}	-40 to +90	°C
Soldering Temperature		T _{slid}	240	°C
Acceptance angle at 50% S _λ		φ	120	deg.

Optical and Electrical Characteristics

T_{amb} = 25°C, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Breakdown voltage ¹⁾	I _R = 10 μA	V _R	5			V
Dark current	V _R = 5 V	I _D		40	200	pA
Responsivity at 740 nm ¹⁾	V _R = 0 V	S _λ		0.5		A/W
Spectral range at 10 %	V _R = 0 V	λ _{0.5}	680		770	nm
Spectral bandwidth at 50%	V _R = 0 V	Δλ _{0.4}		115		nm
Shunt resistance	V _R = 10 mV	R _{SH}		350		GΩ
Noise equivalent power	λ = 740 nm	NEP		7.2x10 ⁻¹⁵		W/√Hz
Specific detectivity	λ = 740 nm	D*		4.2x10 ¹²		cm · √Hz · W ⁻¹
Junction capacitance	V _R = 0 V	C _J		40		pF
Switching time	V _R = 5 V	t _r , t _f		15/30		ns
Photo-current at λ _p ²⁾	V _R = 0 V E _e = 1mW/cm ²	I _{Ph}		760		nA

¹⁾for information only

²⁾Halogen lamp source with appropriate filter

Note: All measurements carried out with *EPIGAP* equipment

Labeling

Type	Lot N°	R _D (typ.) [GΩ]	Quantity
EPD-740-9-0.4			

